RFMD® Will Host In-Booth Demonstrations of GaN High Power Amplifier and Smart Energy Products

RF Micro Devices, Inc. will showcase its broad portfolio of industry-leading RF communications components at the IEEE International Microwave Symposium (IMS). During the conference, RFMD will host in-booth demonstrations of the Company's high-power gallium nitride (GaN) products as well as the Company's smart energy/advanced metering infrastructure (AMI) Zigbee® products. RFMD's GaN in-booth demonstration will feature the RFG1M09180, a high power, high efficiency GaN Doherty amplifier for 3G/4G cellular base stations. The RFG1M09180 achieves 180W peak power at 50V operation while maintaining over 70% peak efficiency, and a single RFG1M09180 amplifier can cover a frequency range of 700 MHz to 1000 MHz. RFMD's smart energy/AMI demonstration will feature RFMD's Zigbee® products developed in collaboration with Ember Corporation for the RF6525/EM357 reference design. RFMD's broad portfolio of RF components serves more than 20 end markets and a very broad, diverse global customer base. RFMD launched more than 350 new and derivative products in support of these markets in the past fiscal year. RFMD's employees presenting papers, chairing sessions and hosting proceedings at the IEEE International Microwave Symposium will represent the Company's Defense and Power, Broadband Components, Wireless Connectivity, Wireless Products, and GaN Foundry Services business units. RFMD will be located at the IEEE International Microwave Symposium (IMS) in Booth 810 in the Exhibition Hall.

Source URL (retrieved on *09/02/2014 - 1:48am*):
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